Supplementary Information

PH modulated memristive behavior based on edible garlic constructed bio-electronic device

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Figure S1. Preparation of garlic powder.



Figure S2. Flow chart for preparation garlic powder.



Figure S3. XRD spectra of garlic powder.



Figure S4. EDX spectrum of the memory device with Ag/Garlic/FTO structure, and the atomic ratios is showed in table.



Figure S5. The memory device functional layer thickness.



Figure S6. The first sweeping cycle current-voltage (I–V) curves on a logarithmic scale.



Figure S7. (a, b) The I–V curves in log–log scale in the positive and negative voltage sweep regions respectively under $pH = \sim 13.0$.